

20. The system of claim 11, wherein at least some of the different wavelength ranges for a particular layer of interest having a vertical stack structure include a longer wavelength range to detect defects on both a surface and throughout a depth of the vertical stack structure and a shorter wavelength range to detect
5 defects on the surface of the vertical stack structure.

21. The method of claim 1, wherein the absorber type material is SiO₂.

22. The system of claim 11, wherein the absorber type material is SiO₂.